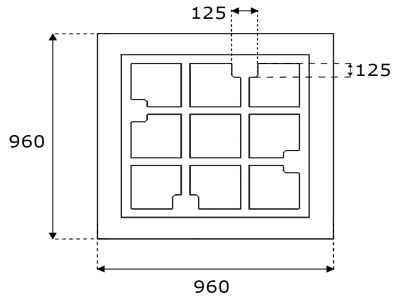
EPIGAP Optronic GmbH
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70

Preliminary Data Sheet

LED Chip Infrared EOLC-750-21

Rev. 04, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs, DDH	N (cathode) up



typ. dimensions (µm)

typ. thickness: 150±25 µm

cathode: gold alloy, thickness 1.5 µm

anode: gold alloy, thickness 0.5 µm,
structured, 25% covered

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		1.5	2.1	V
Forward voltage	I_F=350 mA	V_F		1.9		V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power*	I_F=20 mA	Φ_e	2	2.5		mW
Radiant power*	I_F=350 mA	Φ_e		35		mW
Peak wavelength	I_F=350 mA	λ_p	740	750	760	nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		30		nm
Switching time	I_F=350 mA	t_r, t_f		60		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 045

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.